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- 2 -

AMENDMENTS TO THE SPECIFICATION

At page 8, lines 3-16, please amend the paragraph to read:

Figure 2 illustrates a method of fabricating a ~~silicon~~ silicon nitride dielectric layer. A wafer is cleaned using hydrofluoric acid (HF) or any other suitable cleaning technique 201. A silicon-containing material, is vapor deposited over the wafer 202 from a silicon source such as HMDS. The silicon-containing material can be deposited using a vapor priming (VP) step. Conventionally, vapor priming is one method that has been used, for example, to minimize the amount of photoresist needed during a patterning process. The vapor prime helps "pre-wet" the semiconductor wafer and allows photoresist to flow out more smoothly, and thus more homogeneously. A dielectric layer is fabricated by rapid thermal nitridization (RTN) of the deposited material in an ammonia nitrogen (NH<sub>3</sub>) ambient 203. The resulting dielectric layer is primarily nitride.